



## Initial Product/Process Change Notification

Document #: IPCN23660XA

Issue Date: 16 Mar 2021

<b>Title of Change:</b>	Additional wafer fabrication facility for ONBCD25 technology in ON Semiconductor Aizu located in Aizu, Japan.	
<b>Proposed First Ship date:</b>	30 Apr 2022 or earlier if approved by customer	
<b>Contact Information:</b>	Contact your local ON Semiconductor Sales Office or <a href="mailto:Jiri.Konarik@onsemi.com">Jiri.Konarik@onsemi.com</a>	
<b>PCN Samples Contact:</b>	Contact your local ON Semiconductor Sales Office or <a href="mailto:PCN.samples@onsemi.com">&lt;PCN.samples@onsemi.com&gt;</a> . Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.	
<b>Type of Notification:</b>	This is an Initial Product/Process Change Notification (IPCN) sent to customers. An IPCN is an advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan. The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN). This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change. In case of questions, contact <a href="mailto:PCN.Support@onsemi.com">&lt;PCN.Support@onsemi.com&gt;</a>	
<b>Marking of Parts/ Traceability of Change:</b>	No change	
<b>Change Category:</b>	Wafer Fab Change	
<b>Change Sub-Category(s):</b>	Manufacturing Site Addition	
<b>Sites Affected:</b>		
<b>ON Semiconductor Sites</b>	<b>External Foundry/Subcon Sites</b>	
ON Semiconductor Aizu, Japan	None	
<b>Description and Purpose:</b>		
<p>Based on IPCN23660X. ON Semiconductor would like to inform its customers of additional wafer fabrication facility for ONBCD25 technology in Aizu ON Semiconductor Manufacturing located in Aizu, Japan for the devices listed in this IPCN.</p> <p>All products listed here will be dual sourced from its current wafer fab facility in ON Semiconductor wafer fab in Gresham, US and AFSM, Japan.</p> <p>There is no change to the orderable part number.</p> <p>There is no product marking change as a result of this change.</p>		
	<b>Before Change Description</b>	<b>After Change Description</b>
Wafer Fab Site	Gresham, US	Gresham, US and Aizu, Japan

**Qualification Plan:**

QV DEVICE NAME NCP1251BSN65T1G

PACKAGE: TSOP-6

Test	Specification	Condition	Interval
HTOL	JESD22-A108	TA=125C, bias at 1.2X Nominal (not to exceed Max rated)	1008 hrs
HTSL	JESD22-A103	Ta= 150	1008 hrs
PC	J-STD-020 JESD-A113	IR reflow at 245C or 260C (pkg dependant)	
TC+PC	JESD22-A104	Temp = -55°C to +150°C	500 cyc
HAST+PC	JESD22-A110	Temp = 130C, 85% RH, ~ 18.8 psig bias = 100% of rated V or 100V max	96 hrs
UHAST+PC	JESD22-A118	Temp = 130C, RH=85%, ~ 18.8 psig	96 hrs
SAT	as outlined in MSB17722C	12MSB17722C	
ESD	12MSB17722C	HBM, CDM, IEC	
LU	JESD78	-LU, +LU	

Estimated date for qualification completion: 31 December 2021

**List of Affected Parts:**

**Note:** Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the [PCN Customized Portal](#).

Part Number	Qualification Vehicle
NCP1239DD65R2G	NCP1251ASN65T1G
NCP1239ID65R2G	NCP1251ASN65T1G
NCP1937C61DR2G	NCP1251ASN65T1G
NCP1937A2DR2G	NCP1251ASN65T1G
NCP1937C4DR2G	NCP1251ASN65T1G